

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Tran, Mai-Huong

Sheet 1 of 2

Attorney Docket No: 303.716US2

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
	US-4,161,038	07/10/1979	Wu, S.	365	145	09/20/1977
	US-5,403,788	04/04/1995	Nishida, M. , et al.	501	32	04/21/1994
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	US-5,744,374	04/28/1998	Moon, Jong	437	60	11/18/1996
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		CHO, I. H., "Highly Reliable Dual Gate Oxide Fabrication by Reducing Wet Etching Time and Re-Oxidation for Sub-Quarter Micron CMOS Devices", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , (1999),pgs. 174-175	
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		HAN, B. M., "Chopping effect on the crystallinity of ZnO films prepared by a r.f. planar magnetron sputtering method", <u>Thin Solid Films</u> , 338, (1999),pp. 265-268	
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		NISHINO, J. , "Preparation of Zinc Oxide Films by Low-Pressure Chemical	

EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE                  STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>	Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 40%;"><b>Application Number</b></td> <td>Unknown</td> </tr> <tr> <td><b>Filing Date</b></td> <td>Even Date Herewith</td> </tr> <tr> <td><b>First Named Inventor</b></td> <td>Ahn, Kie</td> </tr> <tr> <td><b>Group Art Unit</b></td> <td>Unknown</td> </tr> <tr> <td><b>Examiner Name</b></td> <td>Tran, Mai-Huong</td> </tr> </table>	<b>Application Number</b>	Unknown	<b>Filing Date</b>	Even Date Herewith	<b>First Named Inventor</b>	Ahn, Kie	<b>Group Art Unit</b>	Unknown	<b>Examiner Name</b>	Tran, Mai-Huong
<b>Application Number</b>	Unknown										
<b>Filing Date</b>	Even Date Herewith										
<b>First Named Inventor</b>	Ahn, Kie										
<b>Group Art Unit</b>	Unknown										
<b>Examiner Name</b>	Tran, Mai-Huong										
Sheet 2 of 2	Attorney Docket No: 303.716US2										

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		Vapor Deposition Method", <u>Mat. Res. Soc. Symp. Proc.</u> 363, (1995),pp. 219-224	
		ONODERA, A. , "Dielectric Activity and Ferroelectricity in Piezoelectric Semiconductor Li-Doped ZnO", <u>Jpn. J. Appl. Phys.</u> , 35, (1996),pp. 5160-5162	
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EXAMINER

DATE CONSIDERED

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	303.716US2
Title:	STRUCTURES, METHODS, AND SYSTEMS FOR FERROELECTRIC MEMORY TRANSISTORS		

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**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Patent Application  
Assistant Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. § 1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/809560, filed on March 15, 2001, which is relied upon for an earlier filing date under 35 U.S.C. § 120.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.


Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date 20 June 2003

By   
Eduardo E. Drake  
Reg. No. 40,594

"Express Mail" mailing label number: EV332569295US

Date of Deposit: June 20, 2003

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to The Commissioner for Patents, Mail Stop Patent Application, P.O.Box 1450, Alexandria, VA 22313-1450.